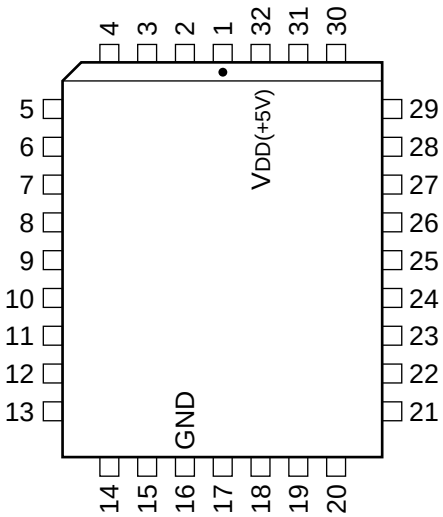
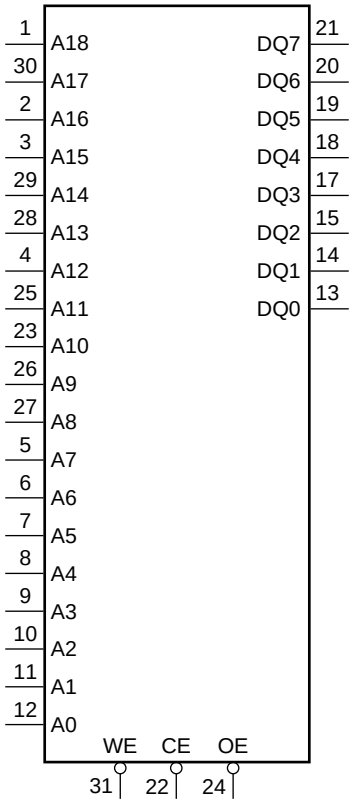
C-MOS 4M (512K 8)-BIT FLASH EEPROM

–TOP VIEW–





(VDD=+5V)

PIN NO.	I/O	SIGNAL	PIN NO.	I/O	SIGNAL
1	I	A18	17	I/O	DQ3
2	I	A16	18	I/O	DQ4
3	I	A15	19	I/O	DQ5
4	I	A12	20	I/O	DQ6
5	I	A7	21	I/O	DQ7
6	I	A6	22	I	$\overline{CE}$
7	I	A5	23	I	A10
8	I	A4	24	I	$\overline{OE}$
9	I	A3	25	I	A11
10	I	A2	26	I	A9
11	I	A1	27	I	A8
12	I	A0	28	I	A13
13	I/O	DQ0	29	I	A14
14	I/O	DQ1	30	I	A17
15	I/O	DQ2	31	I	$\overline{WE}$
16	–	GND	32	–	VDD

INPUT

A0 - A18 ; ADDRESS INPUTS
A0-A7 : SELECTS BYTE WITHIN SECTOR
A8-A18 : SELECTS SECTOR

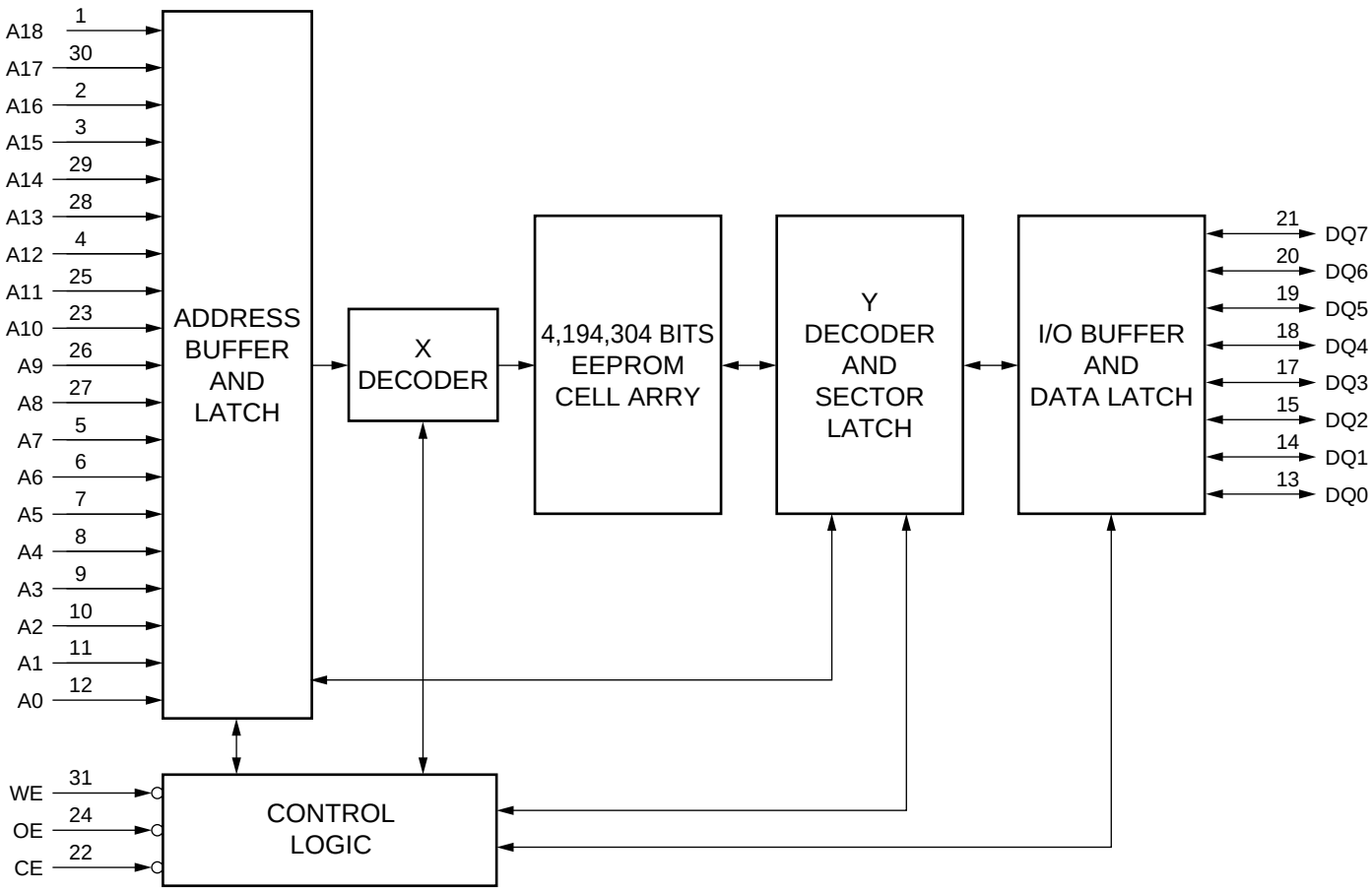
$\overline{CE}$; CHIP ENABLE

$\overline{OE}$; OUTPUT ENABLE

$\overline{WE}$; WRITE ENABLE

INPUT/OUTPUT

DQ0-DQ7 ; DATA INPUT/OUTPUT



Mode	CE	OE	WE	Address	I/O
Read	L	L	H	A_{IN}	D_{OUT}
Erase or Program	L	H	L	A_{IN}	D_{IN}
Standby	H	X	X	X	High Z
Write Inhibit	X	L	X	X	High Z or D_{OUT}
Write Inhibit	X	X	H	X	High Z or D_{OUT}
Product ID	L	L	H	A_9 = 12V, A_0 = V_{IL}	
				$A_{1\text{-}8, 10\text{-}18}$ = V_{IL}	MFG. Code = BF H
				A_0 = V_{IH}	Device Code = 04 H
Chip Erase	L	H	L	X	Set-up Code = 30 H
					Execute Code = 30 H

X = don't care